

838um×838um Silicon PD Chip datasheet

P/N : WS9K-01A

Application

Si PIN photodiode chips.

Structure

Planar type : PIN diode

Electrodes :

Top side (Cathode) : Al

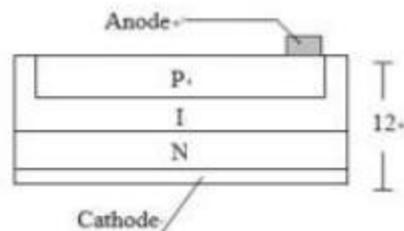
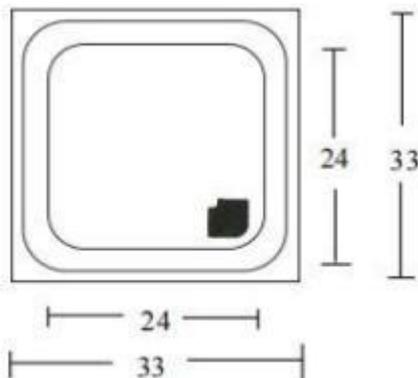
Backside (Anode) : Au Alloy

DIMENSIONS

Conditions	Min.	Typ.	Max.	Unit
Active	24 × 24 (± 1.0)			mil
Chip width	33 × 33 (± 1.5)			mil
Chip length	33 × 33 (± 1.5)			mil
Chip height	12 (± 1.0)			mil
Pad N(Cathode)	5.6 × 5.6			mil
Pad P(Anode)	5.6 × 5.6			mil

Electro-Optical Characteristics (@ Ta =25 °C)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Forward Voltage	VF	IF=10mA, H=0	0.5		1.3	V
Reverse Voltage	VBR	IR=100μA, H=0	35			V
Reverse Dark Current	ID	VR=10V, H=0			10	nA
Sensitive Wavelength Range	λp			940		nm
Capacitance	CJ	VR=3V, F=1 MHz		9		pF



Unit : mil